GaAs INFRARED EMITTING DIODE

PACKAGE DIMENSIONS 0.209 (5.31) 0.184 (4.67) 0.030 (0.76) 0.155 (3.94) NQM MAX 1.00 (25.4) MIN ANODE (CASE) 0.100 (2.54) - 0.050 (1.27) 0.040 (1.02) Ø0.020 (0.51) 2X 0.040 (1.02) NOTES:

- 1. Dimensions for all drawings are in inches (mm).
- 2. Tolerance of \pm .010 (.25) on all non-nominal dimensions unless otherwise specified.

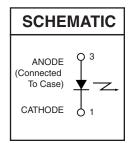
FEATURES

- · Good optical to mechanical alignment
- Mechanically and wavelength matched to the TO-18 series phototransistor
- · Hermetically sealed package
- High irradiance level
- (*) Indicates JEDEC registered values



DESCRIPTION

 The 1N6265 is a 940 nm LED in a narrow angle, TO-46 package.



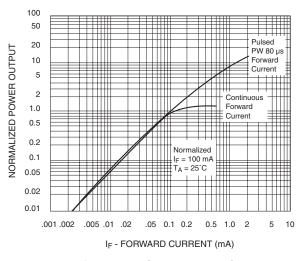
- 1. Derate power dissipation linearly 1.70 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 13.0 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension
- 7. Total power output, P_O , is the total power radiated by the device into a solid angle of 2 π steradians.

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Unit					
Operating Temperature	T _{OPR}	-65 to +125	°C					
*Storage Temperature	T _{STG}	-65 to +150	°C					
*Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C					
*Soldering Temperature (Flow)(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C					
*Continuous Forward Current	I _F	100	mA					
*Forward Current (pw, 1µs; 200Hz)	I _F	10	A					
*Reverse Voltage	V _R	3	V					
*Power Dissipation (T _A = 25°C) ⁽¹⁾	P _D	170	mW					
Power Dissipation $(T_0 = 25^{\circ}C)^{(2)}$	Pp	1.3	W					

ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)							
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS	
*Peak Emission Wavelength	$I_F = 100 \text{ mA}$	λ_{PE}	935	_	955	nm	
Emission Angle at 1/2 Power		θ	_	±40	_	Deg.	
*Forward Voltage	I _F = 100 mA	V_{F}	_	_	1.7	V	
*Reverse Leakage Current	V _R = 3 V	I _R	_	_	10	μA	
*Total Power	I _F = 100 mA	Po	6	_	_	mW	
Rise Time 0-90% of output		t _r	_	1.0	_	μs	
Fall Time 100-10% of output		t_f	_	1.0	_	μs	



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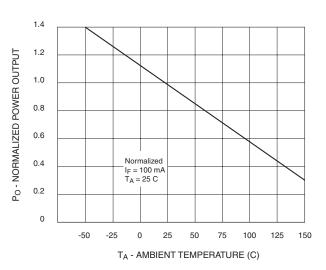


Fig. 2 Power Output vs. Temperature

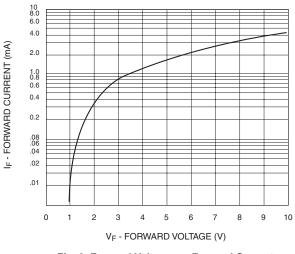


Fig. 3 Forward Voltage vs. Forward Current

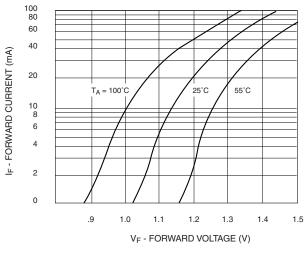
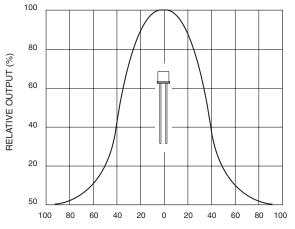


Fig. 4 Forward Voltage vs. Forward Current



 $\boldsymbol{\theta}$ - ANGULAR DISPLACEMENT FROM OPTICAL AXIS DEGREES

Fig. 5 Typical Radiation Pattern



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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.